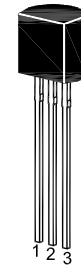


# 2SC3112

## NPN Silicon Epitaxial Planar Transistor

for general purpose and switching applications.



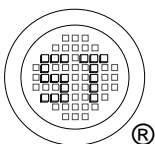
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	50	V
Collector Emitter Voltage	$V_{CEO}$	50	V
Emitter Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	150	mA
Base Current	$I_B$	30	mA
Power Dissipation	$P_{tot}$	300	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

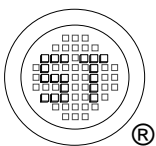
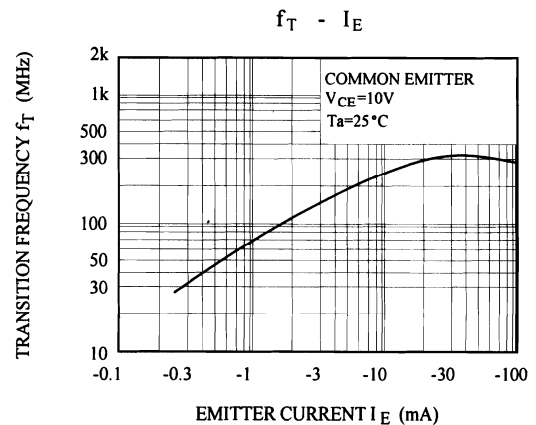
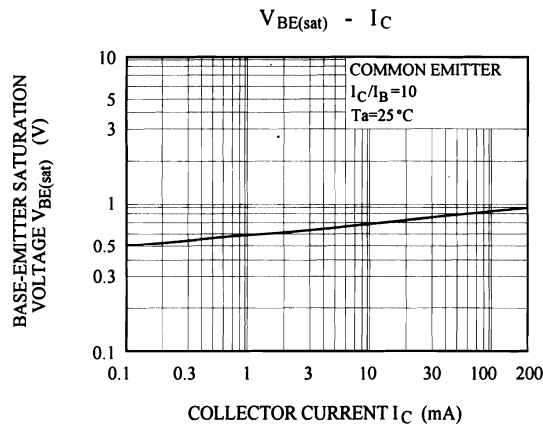
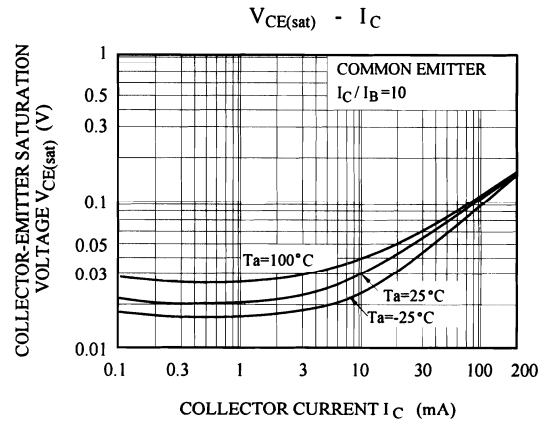
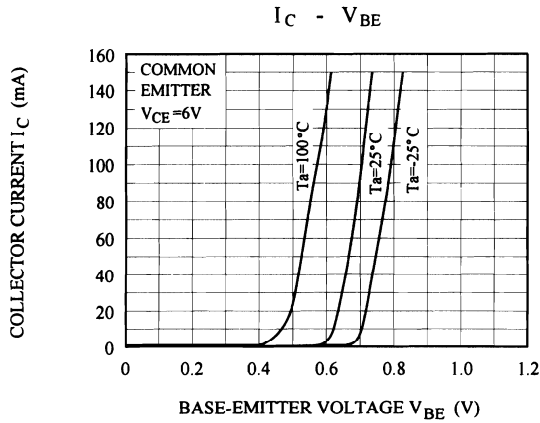
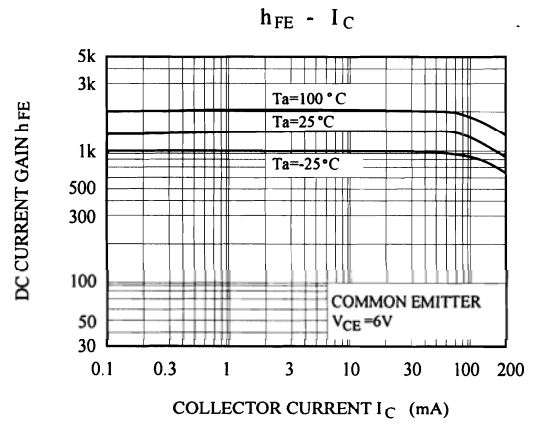
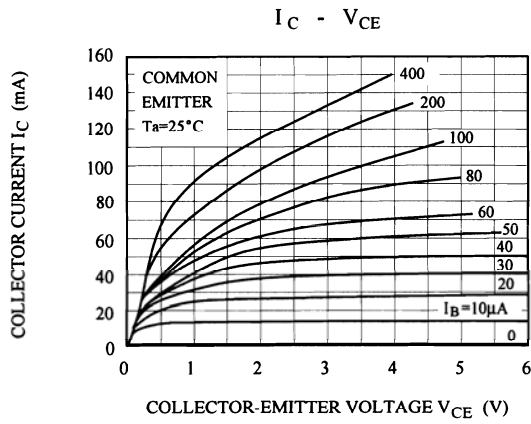
### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 6\text{ V}$ , $I_C = 2\text{ mA}$	Current Gain Group A	$h_{FE}$	600	-	1800	-
	B	$h_{FE}$	1200	-	3600	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	$I_{CBO}$	-	-	100	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	$I_{EBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	-	V	
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V	
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$ , $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	-	0.25	V	
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$ , $I_C = 10\text{ mA}$	$f_T$	100	-	-	MHz	
Collector Output Capacitance at $V_{CB} = 10\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$	$C_{ob}$	-	3.5	-	pF	



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